## **250 18 13**

NPN SILICON TRANSISTOR

2SC1815 is NPN silicon epitaxial transistor designed for RF, AF amplifier and general purpose applications.



## ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage	$V_{CBO}$	45V
Collector-Emitter Voltage	V <sub>CEO</sub>	40V
Emitter-Base Voltage	$v_{EBO}$	5V
Collector Current	$I_{C}$	100mA
Total Power Dissipation	P <sub>tot</sub>	300mW
Operating Junction and Storage Temperature	T <sub>j</sub> ,T <sub>stg</sub>	-55 to 125°C

## ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise specified)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	TEST CONDITIONS
Collector-Emitter Breakdown Voltage	LVCEO	40	,		V	I <sub>C</sub> =10mA I <sub>B</sub> =0*
Collector Cutoff Current	I <sub>CBO</sub>			100	пA	V <sub>CB</sub> =18V I <sub>E</sub> =0
Emitter Cutoff Current	I <sub>EBO</sub>			1	μΑ	V <sub>EB</sub> =5V I <sub>C</sub> =0
D.C. Current Gain Group O Group Y Group GR	HFE	70 70 120 200		700 140 240 400		I <sub>C</sub> =2mA V <sub>CE</sub> =6V
Group BL Collector-Emitter Saturation Voltage	V <sub>CE</sub> (sat)	350		<b>700</b> 0.4	٧	I <sub>C</sub> =10mA I <sub>B</sub> =1mA
Current Gain-Bandwidth Product	fŢ	80	200		MHz	I <sub>C</sub> =1mA V <sub>CE</sub> =10V
Output Capacitance	Сов		2	3.5	pF	V <sub>CB</sub> =10V f=1MHz

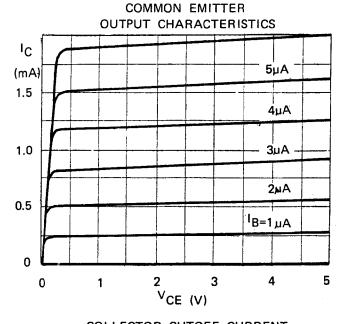
\* Pulse Test : Pulse Width = 300µS, Duty Cycle = 1%.

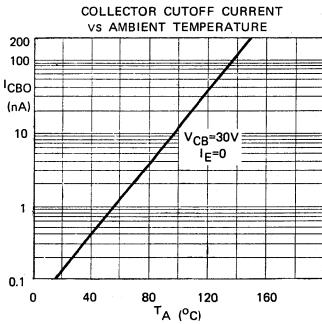


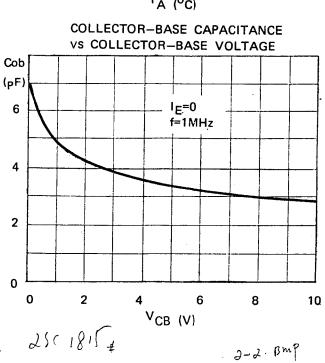
MICRO ELECTRONICS LTD. 美科有限公司

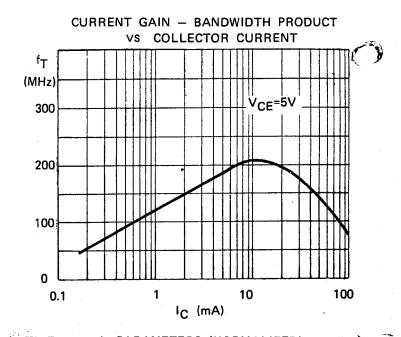
38 Hung To Road, Kwun Tong, Kowloon, Hong Kong. Cable: Microtron, Hong Kong. Telex: 43510 Micro HX.

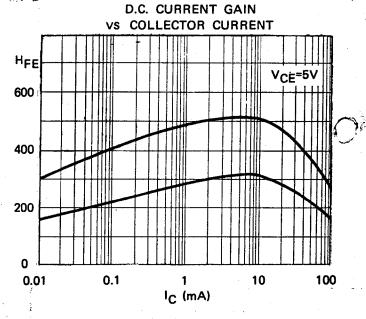
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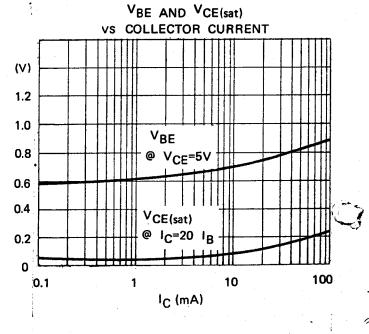












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